

## PNP General Purpose Transistor

**BC856T/BC857T**

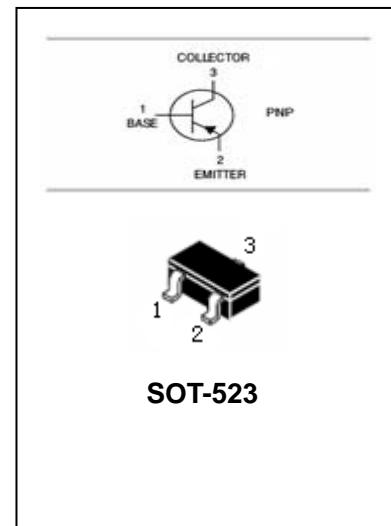
### FEATURES

- Low current(max.100mA).
- Low voltage(max.65V).



### APPLICATIONS

- General purpose switching and amplification,especially  
In portable equipment.



### ORDERING INFORMATION

Type No.	Marking	Package Code
BC856AT	3A	SOT-523
BC856BT	3B	SOT-523
BC857AT	3E	SOT-523
BC857BT	3F	SOT-523
BC857CT	3G	SOT-523

### MAXIMUM RATING @ $T_a=25^{\circ}\text{C}$ unless otherwise specified

Symbol	Parameter	Limits	Unit
$V_{CBO}$	collector-base voltage BC856AT; BC856BT BC857AT; BC857BT; BC857CT	-80 -50	V
$V_{CEO}$	collector-emitter voltage BC856AT; BC856BT BC857AT; BC857BT; BC857CT	-65 -45	V
$V_{EBO}$	emitter-base voltage	-5	V
$I_C$	collector current	-100	mA
$I_{CM}$	peak collector current	-200	mA
$I_{BM}$	peak base current	-100	mA
$P_{tot}$	Total power dissipation	150	mW
$R_{\theta JA}$	Thermal resistance, junction to Ambient	833	°C/W
$T_{stg}$	storage temperature range	-65 to +150	°C
$T_j$	junction temperature	150	°C

**PNP General Purpose Transistor****BC856T/BC857T**ELECTRICAL CHARACTERISTICS @  $T_a=25^\circ\text{C}$  unless otherwise specified

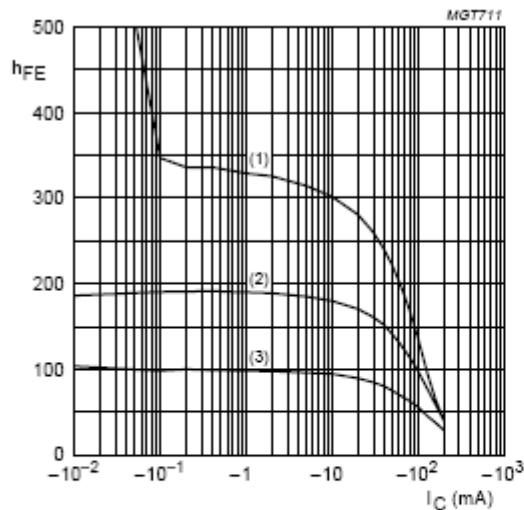
SYMBOL	PARAMETER	CONDITIONS	MIN.	Typ.	MAX.	UNIT
$V_{(\text{BR})\text{CBO}}$	Collector-base breakdown voltage BC856AT; BC856BT BC857AT; BC857BT; BC857CT	$I_C=-10\mu\text{A}, I_E=0$	-80 -50			V
$V_{(\text{BR})\text{CEO}}$	Collector-emitter breakdown voltage BC856AT; BC856BT BC857AT; BC857BT; BC857CT	$I_C=-10\text{mA}, I_B=0$	-65 -45			V
$V_{(\text{BR})\text{EBO}}$	Emitter-base breakdown voltage	$I_E=-1\mu\text{A}, I_C=0$	-5			V
$I_{\text{CBO}}$	Collector cut-off current	$I_E=0, V_{\text{CB}}=-30\text{V}$			-15	nA
		$I_E=0, V_{\text{CB}}=-30\text{V}, T_j=150^\circ\text{C}$			-5	uA
$I_{\text{EBO}}$	Emitter cut-off current	$I_C=0, V_{\text{EB}}=-5\text{V}$			-100	nA
$h_{\text{FE}}$	DC current gain BC856AT; BC857AT BC856BT; BC857BT BC857CT	$V_{\text{CE}}=-5\text{V}, I_C=-2\text{mA}$	125	-	250	
			220	-	475	
			420	-	800	
$V_{\text{CE}(\text{sat})}$	collector-emitter saturation voltage	$I_C=-10\text{mA}, I_B=-0.5\text{mA}$			-200	mV
		$I_C=-100\text{mA}, I_B=-5\text{mA}(\text{note1})$			-400	mV
$V_{\text{BE}}$	Base- emitter voltage	$I_C=-2\text{mA}, V_{\text{CE}}=-5\text{V}$	-580		-700	mV
		$I_C=-10\text{mA}, V_{\text{CE}}=-5\text{V}$			-770	mV
$C_{\text{C}}$	Collector capacitance	$I_E=0, V_{\text{CB}}=-10\text{V}, f=1\text{MHz}$			2.5	pF
$C_{\text{e}}$	Emitter capacitance	$I_C=0, V_{\text{EB}}=-0.5\text{V}, f=1\text{MHz}$		10		pF
$F$	Noise figure	$I_C=200\mu\text{A}, V_{\text{CE}}=-5\text{V}, R_S=2\text{k}\Omega, f=1\text{kHz}, B=200\text{Hz}$			10	dB
$f_T$	transition frequency	$I_C=-10\text{mA}, V_{\text{CE}}=-5\text{V}, f=100\text{MHz}$	100			MHz

Note 1.Pulse test: $t_p \leq 300\mu\text{s}; \delta \leq 0.02$

## PNP General Purpose Transistor

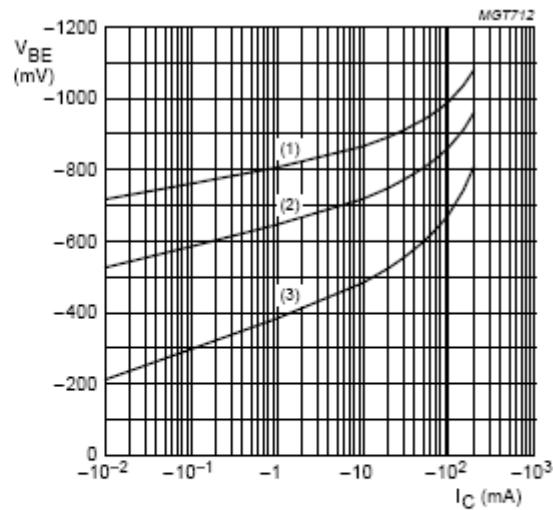
**BC856T/BC857T**

TYPICAL CHARACTERISTICS @  $T_a=25^\circ\text{C}$  unless otherwise specified



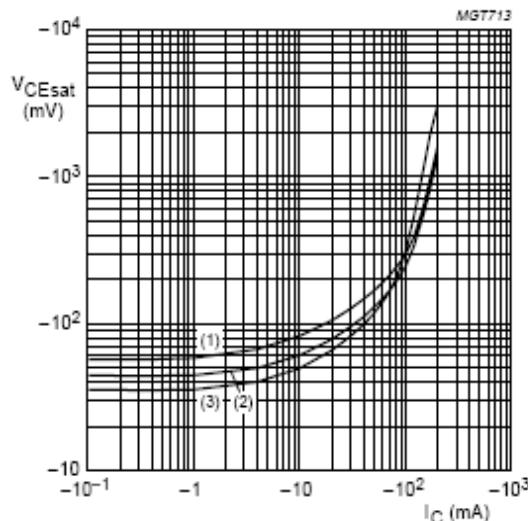
$V_{CE} = -5 \text{ V}$ .  
(1)  $T_{amb} = 150^\circ\text{C}$ .  
(2)  $T_{amb} = 25^\circ\text{C}$ .  
(3)  $T_{amb} = -55^\circ\text{C}$ .

Fig.2 DC current gain; typical values.



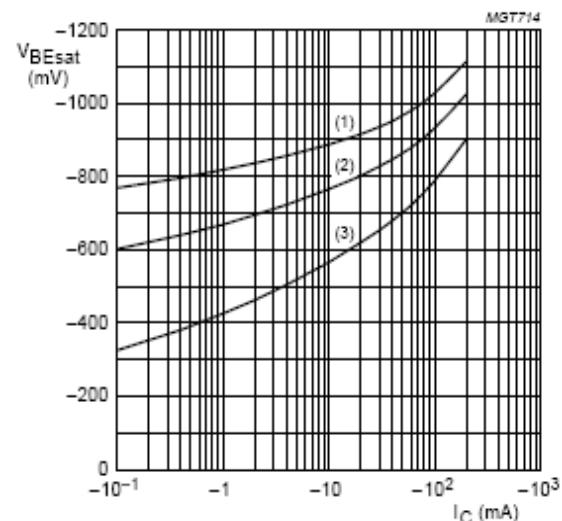
$V_{CE} = -5 \text{ V}$ .  
(1)  $T_{amb} = -55^\circ\text{C}$ .  
(2)  $T_{amb} = 25^\circ\text{C}$ .  
(3)  $T_{amb} = 150^\circ\text{C}$ .

Fig.3 Base-emitter voltage as a function of collector current; typical values.



$I_C/I_B = 20$ .  
(1)  $T_{amb} = 150^\circ\text{C}$ .  
(2)  $T_{amb} = 25^\circ\text{C}$ .  
(3)  $T_{amb} = -55^\circ\text{C}$ .

Fig.4 Collector-emitter saturation voltage as a function of collector current; typical values.

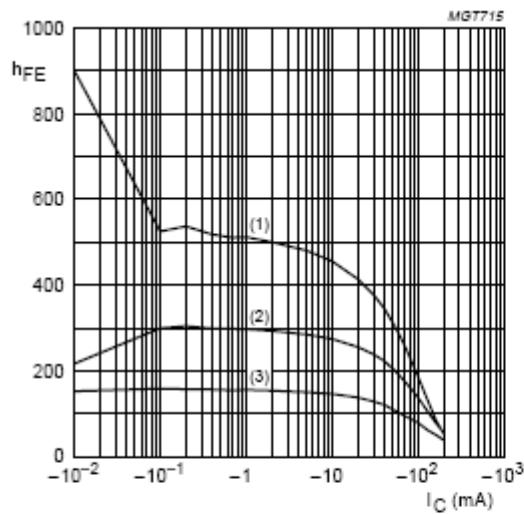


$I_C/I_B = 20$ .  
(1)  $T_{amb} = -55^\circ\text{C}$ .  
(2)  $T_{amb} = 25^\circ\text{C}$ .  
(3)  $T_{amb} = 150^\circ\text{C}$ .

Fig.5 Base-emitter saturation voltage as a function of collector current; typical values.

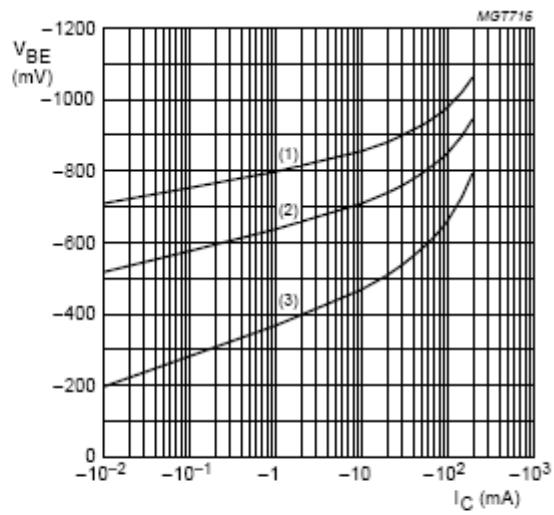
## PNP General Purpose Transistor

## BC856T/BC857T



$V_{CE} = -5$  V.  
(1)  $T_{amb} = 150$  °C.  
(2)  $T_{amb} = 25$  °C.  
(3)  $T_{amb} = -55$  °C.

Fig.6 DC current gain; typical values.



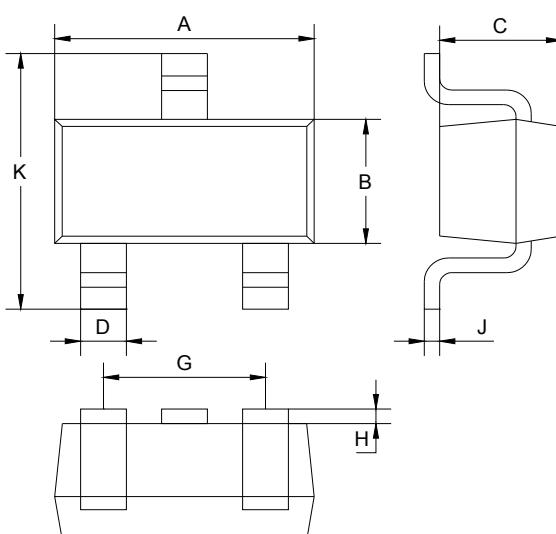
$V_{CE} = -5$  V.  
(1)  $T_{amb} = -55$  °C.  
(2)  $T_{amb} = 25$  °C.  
(3)  $T_{amb} = 150$  °C.

Fig.7 Base-emitter voltage as a function of collector current; typical values.

## PACKAGE OUTLINE

Plastic surface mounted package

SOT-523

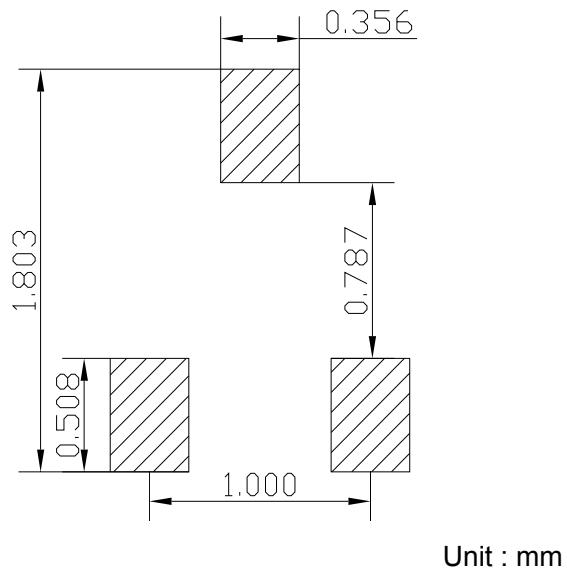


SOT-523		
Dim	Min	Max
A	1.5	1.7
B	0.75	0.85
C	0.6	0.8
D	0.15	0.3
G	0.9	1.1
H	0.02	0.1
J	0.1Typical	
K	1.45	1.75
All Dimensions in mm		

## PNP General Purpose Transistor

**BC856T/BC857T**

### SOLDERING FOOTPRINT



Unit : mm

### PACKAGE INFORMATION

Device	Package	Shipping
BC856T/BC857T	SOT-523	3000/Tape&Reel